

Transistor

**Panasonic**

# 2SD661, 2SD661A

Silicon NPN epitaxial planer type

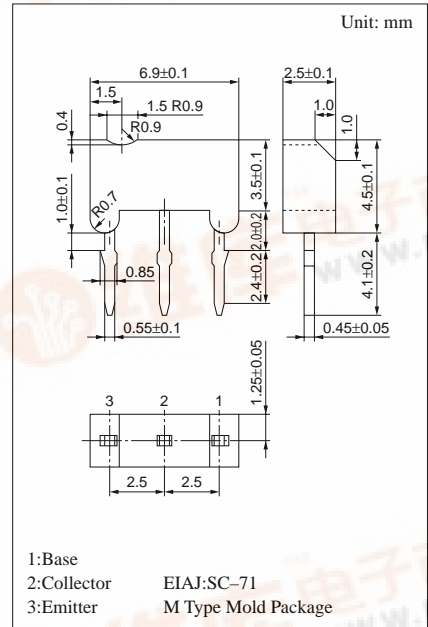
For low-frequency and low-noise amplification

## Features

- Low noise voltage NV.
- High forward current transfer ratio  $h_{FE}$ .
- M type package allowing easy automatic and manual insertion as well as stand-alone fixing to the printed circuit board.

## Absolute Maximum Ratings (Ta=25°C)

Parameter	Symbol	Rated	Unit	
Collector to base voltage	2SD661 2SD661A	$V_{CBO}$	35	V
			55	
Collector to emitter voltage	2SD661 2SD661A	$V_{CEO}$	35	V
			55	
Emitter to base voltage	$V_{EBO}$	7	V	
Peak collector current	$I_{CP}$	200	mA	
Collector current	$I_C$	100	mA	
Collector power dissipation	$P_C$	400	mW	
Junction temperature	$T_j$	150	°C	
Storage temperature	$T_{stg}$	-55 ~ +150	°C	



## Electrical Characteristics (Ta=25°C)

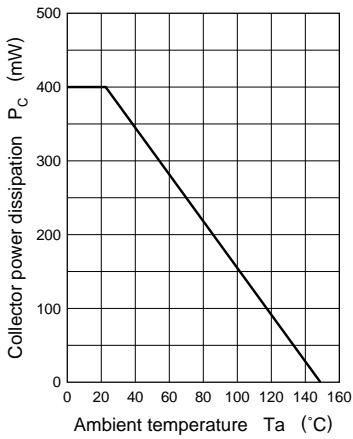
Parameter	Symbol	Conditions	min	typ	max	Unit
Collector cutoff current	$I_{CBO}$	$V_{CB} = 20V, I_E = 0$			0.1	$\mu A$
	$I_{CEO}$	$V_{CE} = 20V, I_B = 0$			1	$\mu A$
Collector to base voltage	2SD661 2SD661A	$V_{CBO}$	$I_C = 10\mu A, I_E = 0$	35		V
				55		
Collector to emitter voltage	2SD661 2SD661A	$V_{CEO}$	$I_C = 2mA, I_B = 0$	35		V
				55		
Emitter to base voltage	$V_{EBO}$	$I_E = 10\mu A, I_C = 0$	7		V	
Forward current transfer ratio	$h_{FE}^*$	$V_{CE} = 10V, I_C = 2mA$	210		650	
Collector to emitter saturation voltage	$V_{CE(sat)}$	$I_C = 100mA, I_B = 10mA$			1	V
Transition frequency	$f_T$	$V_{CB} = 10V, I_E = -2mA, f = 200MHz$		200		MHz
Noise voltage	NV	$V_{CE} = 10V, I_C = 1mA, G_V = 80dB$ $R_g = 100k\Omega, \text{Function} = \text{FLAT}$			150	mV

## $h_{FE}$ Rank classification

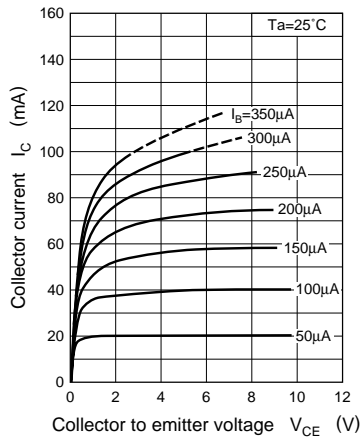
Rank	R	S	T
$h_{FE}$	210 ~ 340	290 ~ 460	360 ~ 650



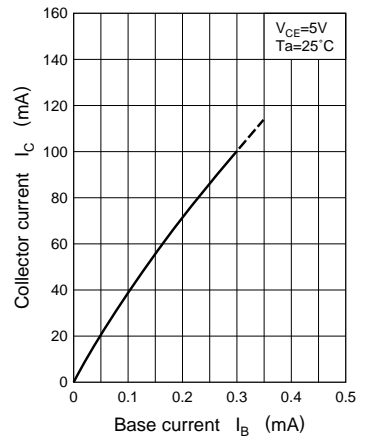
$P_C - T_a$



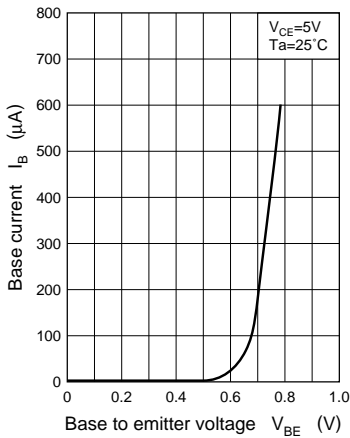
$I_C - V_{CE}$



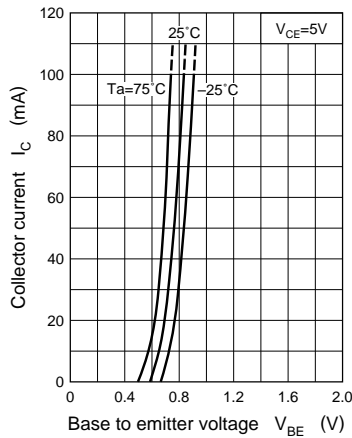
$I_C - I_B$



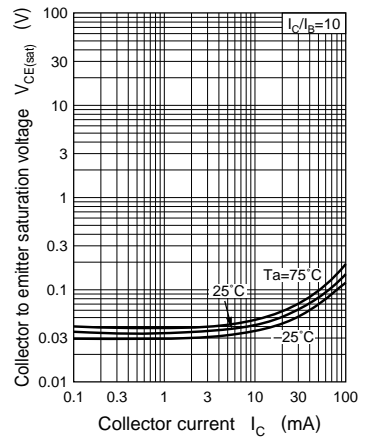
$I_B - V_{BE}$



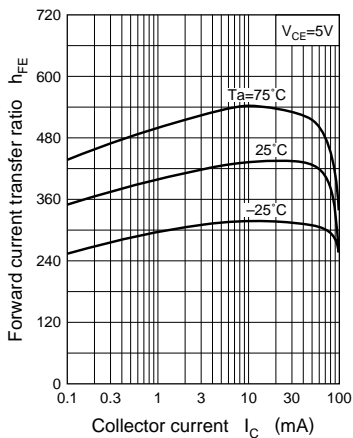
$I_C - V_{BE}$



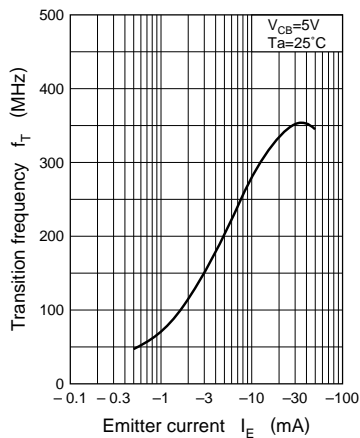
$V_{CE(sat)} - I_C$



$h_{FE} - I_C$



$f_T - I_E$



$C_{ob} - V_{CB}$

